

SCT2160KE N-channel SiC power MOSFET

 $\begin{tabular}{|c|c|c|c|c|} \hline V_{DSS} & 1200V \\ \hline R_{DS(on)}\,(Typ.) & 160m\Omega \\ \hline I_D & 22A \\ \hline P_D & 165W \\ \hline \end{tabular}$

Features

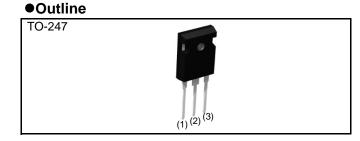
- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating ; RoHS compliant

Application

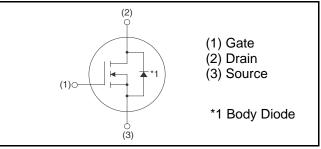
- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating
- Motor drives

•Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V _{DSS}	1200	V
Continuous drain ourrent	$T_c = 25^{\circ}C$	I _D ^{*1}	22	А
Continuous drain current	$T_c = 100^{\circ}C$	I _D ^{*1}	16	А
Pulsed drain current		I _{D,pulse} *2	55	А
Gate - Source voltage (DC)		V _{GSS}	-6 to 22	V
Gate - Source surge voltage (T _{surge} < 300nsec)		V _{GSS-surge} *3	-10 to 26	V
Power dissipation $(T_c = 25^{\circ}C)$		P _D	165	W
Junction temperature		Tj	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C



Inner circuit



Packaging specifications

	Packaging	Tube
	Reel size (mm)	-
Tuno	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Packing code	С
	Marking	SCT2160KE

•Thermal resistance

Parameter	Symbol	Values			Unit
Farameter	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	-	0.70	0.91	°C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	50	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

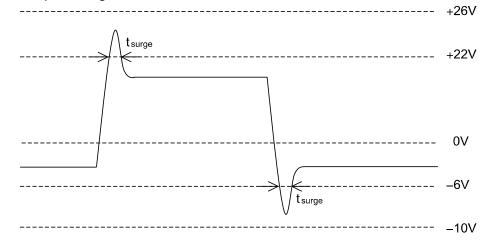
•Electrical characteristics ($T_a = 25^{\circ}C$)

Parameter	Symbol	Conditions	Values			Unit	
Farameter	Symbol Conditions –		Min.	Тур.	Max.	Ont	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	1200	-	-	V	
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 1200V, V_{GS} = 0V$ $T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$	-	1 2	10 -	μΑ	
Gate - Source leakage current	I_{GSS^+}	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA	
Gate - Source leakage current	I _{GSS-}	$V_{GS} = -6V, V_{DS} = 0V$	-	-	-100	nA	
Gate threshold voltage	V _{GS (th)}	$V_{DS} = V_{GS}, I_{D} = 2.5 mA$	1.6	2.8	4.0	V	

*1 Limited only by maximum temperature allowed.

*2 PW \leq 10µs, Duty cycle \leq 1%

*3 Example of acceptable Vgs waveform



*4 Pulsed

•Electrical characteristics ($T_a = 25^{\circ}C$)

Deremeter	Currente al	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Onit
		V _{GS} = 18V, I _D = 7A				
Static drain - source on - state resistance	$R_{DS(on)}^{*4}$	$T_j = 25^{\circ}C$	-	160	208	mΩ
		T _j = 125°C	-	226	-	
Gate input resistance	R _G	f = 1MHz, open drain	-	13.7	-	Ω
Transconductance	g _{fs} *4	$V_{DS} = 10V, I_{D} = 7A$	-	2.4	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	1200	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	45	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	7	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 500V	-	71	-	pF
Turn - on delay time	t _{d(on)} *4	$V_{DD} = 400V, I_{D} = 7A$	-	23	-	
Rise time	t _r *4	V _{GS} = 18V/0V	-	25	-	
Turn - off delay time	t _{d(off)} *4	$R_L = 57\Omega$	-	67	-	ns
Fall time	t _f *4	$R_{G} = 0\Omega$	-	27	-	
Turn - on switching loss	E _{on} *4	$V_{DD} = 600V, I_{D} = 7A$ $V_{GS} = 18V/0V$	-	126	-	
Turn - off switching loss	E _{off} *4	$R_G = 0\Omega$, L=500µH *E _{on} includes diode reverse recovery	-	55	-	μJ

•Gate Charge characteristics ($T_a = 25^{\circ}C$)

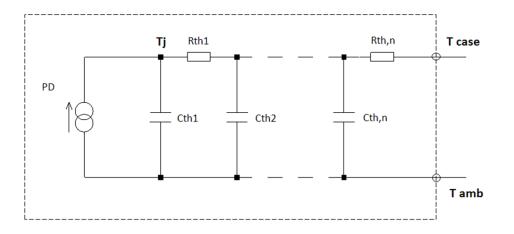
Parameter	Sumbol	Conditions	Values			Unit
Farameter	Symbol Conditions -		Min.	Тур.	Max.	Onit
Total gate charge	Q_g^{*4}	V _{DD} = 400V	-	62	-	
Gate - Source charge	Q_{gs}^{*4}	I _D = 7A	-	14	-	nC
Gate - Drain charge	Q_{gd}^{*4}	V _{GS} = 18V	-	20	-	
Gate plateau voltage	V _(plateau)	$V_{DD} = 400V, I_D = 7A$	-	9.6	-	V

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit	
Farameter	Symbol Conditions –		Min.	Тур.	Max.	Unit	
Inverse diode continuous, forward current	ا _S *1	T _c = 25°C	-	-	22	А	
Inverse diode direct current, pulsed	I _{SM} *2	T _c = 25 C	-	-	55	А	
Forward voltage	V_{SD} *4	$V_{GS} = 0V, I_{S} = 7A$	-	4.1	-	V	
Reverse recovery time	t _{rr} *4		-	26	-	ns	
Reverse recovery charge Q _{rr} ^{*4}		I _F = 7A, V _R = 400V di/dt = 160A/μs	-	39	-	nC	
Peak reverse recovery current	^{*4}		-	3.0	-	А	

•Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
R _{th1}	96.1m		C_{th1}	1.55m	
R _{th2}	404m	K/W	C _{th2}	5.23m	Ws/K
R _{th3}	196m		C_{th3}	83.3m	



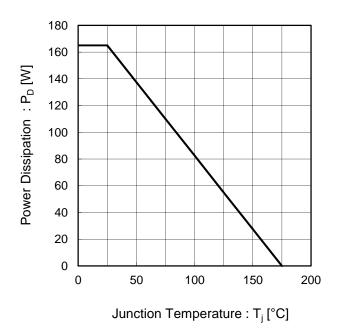
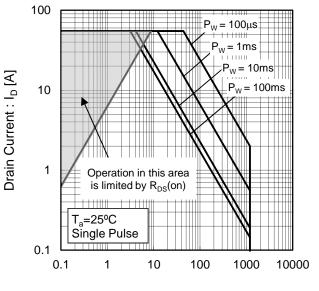
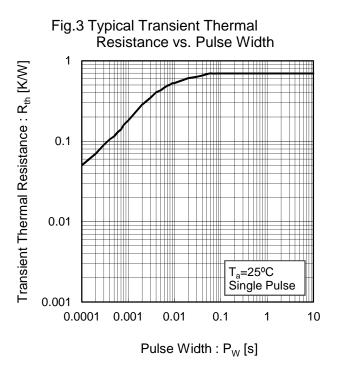


Fig.1 Power Dissipation Derating Curve

Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : V_{DS} [V]



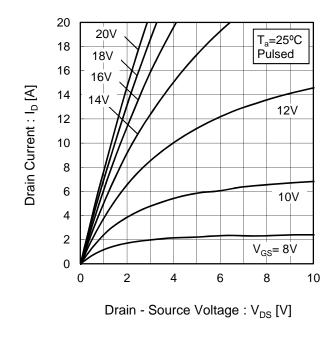
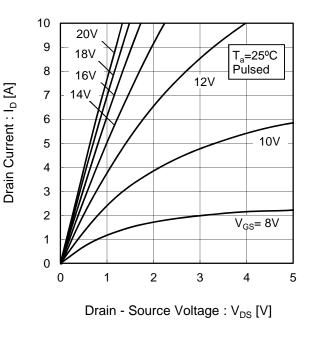
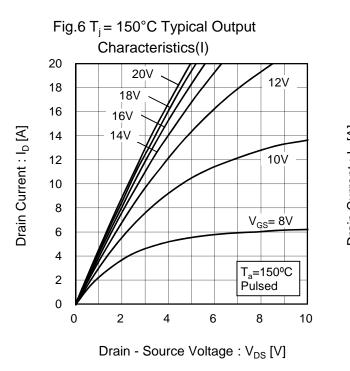
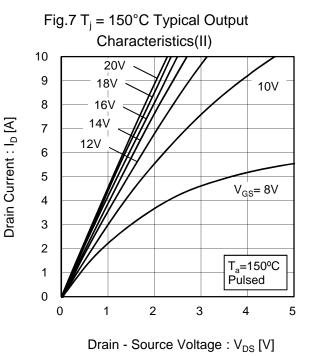


Fig.4 Typical Output Characteristics(I)

Fig.5 Typical Output Characteristics(II)







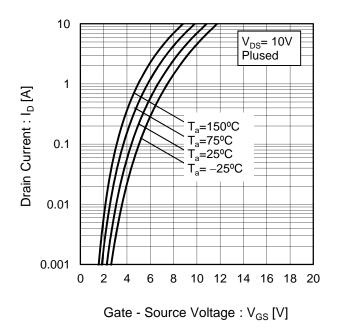


Fig.8 Typical Transfer Characteristics (I)

Fig.9 Typical Transfer Characteristics (II)

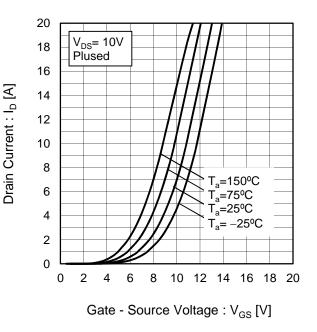
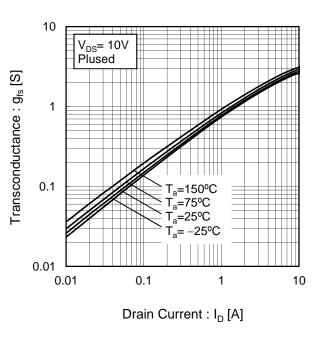


Fig.10 Gate Threshold Voltage vs. Junction Temperature 5 $V_{DS} = 10V$ $I_{D} = 3mA$ 4.5 Gate Threshold Voltage : V_{GS(th)} [V] 4 3.5 3 2.5 2 1.5 1 0.5 0 -50 0 50 100 150 200 Junction Temperature : T_i [°C]

Fig.11 Transconductance vs. Drain Current



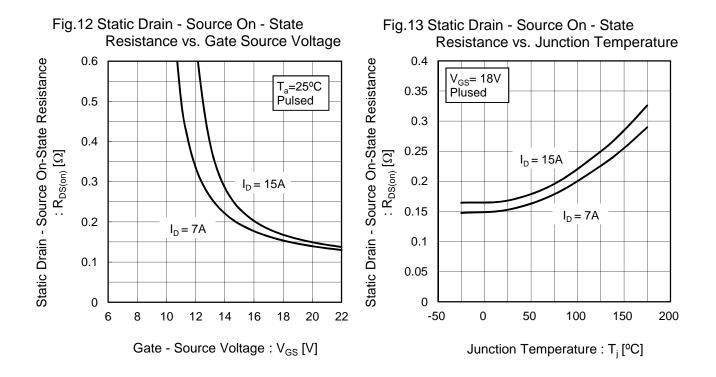


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current Static Drain - Source On-State Resistance 1 V_{GS}= 18V Plused T_a=150°C : R_{DS(on)} [Ω] т̃_=75⁰С T_a=25⁰C T_a= −25°C 0.1 0.1 1 10 100

Drain Current : I_D [A]

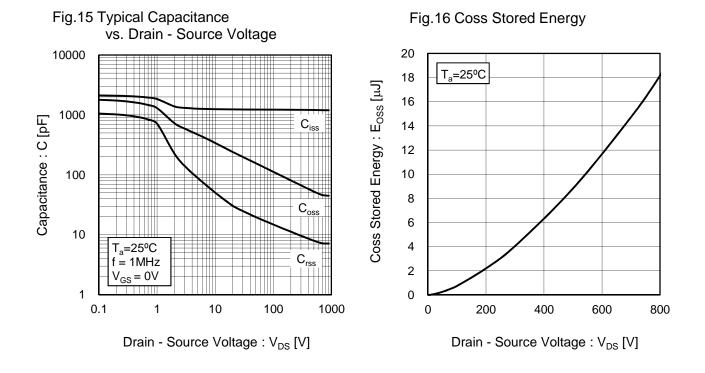
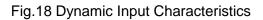
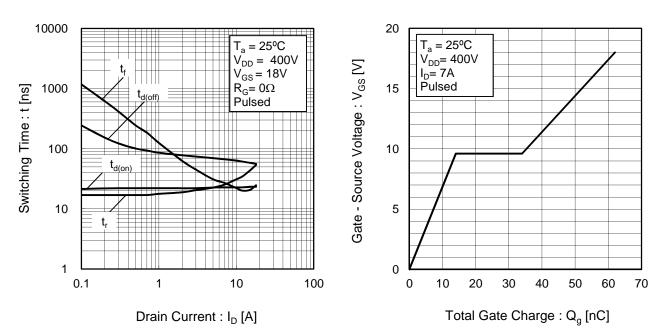
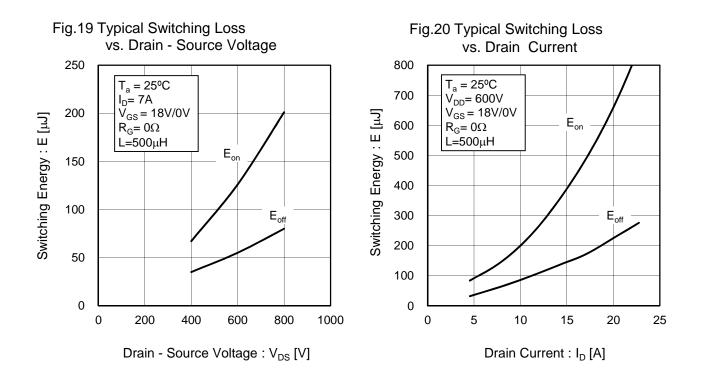


Fig.17 Switching Characteristics







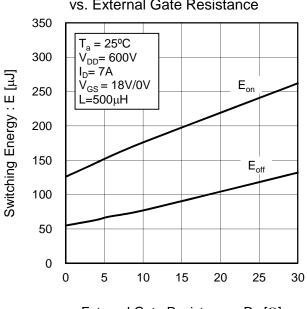
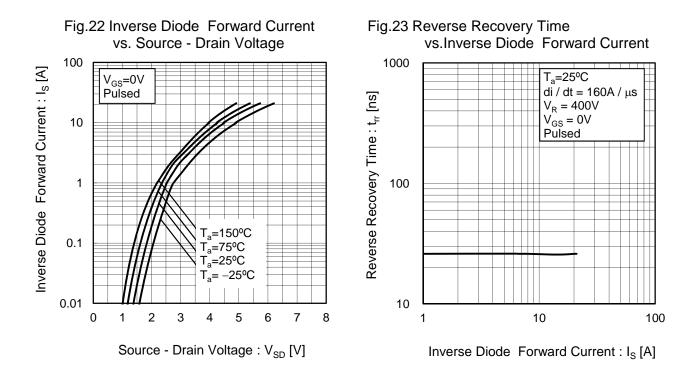




Fig.21 Typical Switching Loss vs. External Gate Resistance





Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

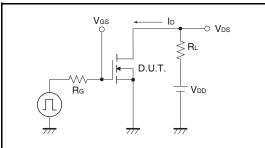


Fig.2-1 Gate Charge Measurement Circuit

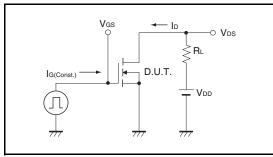


Fig.3-1 Switching Energy Measurement Circuit

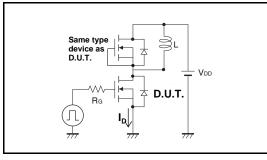


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

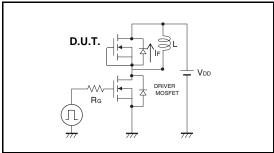


Fig.1-2 Switching Waveforms

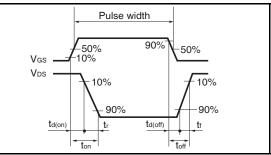


Fig.2-2 Gate Charge Waveform

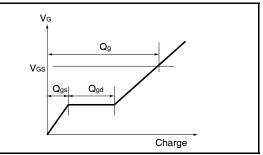
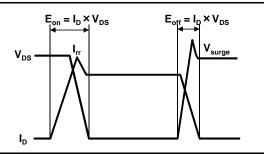
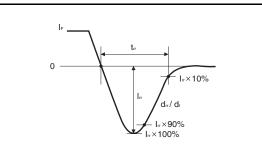


Fig.3-2 Switching Waveforms







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